AMENDMENTS TO THE SPECIFICATION:

Please amend the specification as follows:

Please substitute the paragraph beginning at page 10, line 20, and ending on page 11, line 3, with the following.

-- Electrons emitted from the electron source form a substantially parallel electron beam through a condenser lens 2, whose front focal position is located at the electron source position. The substantially parallel electron beam comes incident on an element electron optical system array 3. The element electron optical system array 3 is formed by arranging a plurality of element electron optical systems, each comprising a blanking electrode, an aperture, and an electron lens, in a plane perpendicular to the Z-axis (an electron optical axis). --

Please substitute the paragraph beginning at page 11, line 4, with the following.

-- The element electron optical system array 3 forms a plurality of intermediate images of the electron source. The respective intermediate images are reduced and projected onto a wafer 5 by a reduction electron optical system 4, to form electron source images on the wafer 5. The respective element electron optical systems of the element electron optical system array 3 are set such that the spacing between adjacent electron source images on the wafer 5 is an integer multiple of the size of each electron source image. Additionally, the element electron optical system array 3 is arranged to differently adjust the position of each intermediate image in the direction of the electron optical axis, in accordance with the curvature of field of the reduction electron optical system 4, and to correct, in advance, an aberration that occurs when each

intermediate image is reduced and projected onto the wafer 5 by the reduction electron optical system 4. --

Please substitute the paragraph beginning at page 15, line 15, with the following.

-- The adoption of a non-contact electromagnetic actuator as described above for use in driving the fine adjustment stage 11 prevents a driving reaction force from appearing upon driving of the fine adjustment stage 11, and contributes to solving a problem of dust generation. --

Please substitute the paragraph beginning at page 15, line 21, and ending on page 16, line 3, with the following.

-- The non-energized I cores 120 are attached to the fine adjustment stage 11, and the E cores 120′ each including a coil are attached to the center slider 12. This arrangement has the advantage in that heat transfer to the fine adjustment stage 11 is remarkably ~~reduces~~ reduced and that the fine adjustment stage 11 has no trailing wires. Such an electromagnetic actuator is excellent in that it generates a relatively large thrust, consumes relative ~~small~~ little power, and generates no leakage magnetic field in a non-energized state. --

Please substitute the paragraph beginning at page 20, line 12, with the following.

-- (3) The controller 20 corrects the non-linearity of a control system (e.g., electromagnetic actuator components 120 and 120′) on the basis of a measurement value from the displacement sensors 202. --

Please substitute the paragraph beginning at page 20, line 16, with the following.

-- To control the fine adjustment stage 11, various other methods are available. With the above-mentioned method, the fine adjustment stage 11 is so controlled as not to be affected by the coarse adjustment stage (center slider) 12 and as to compensate for the non-linearity of the control system (particularly, an electromagnetic ~~actuators~~ actuator). --

Please substitute the paragraph beginning at page 22, line 14, with the following.

-- Fig. 4 is a schematic view showing the main part of an electron beam exposure apparatus according to the second embodiment of the present invention. Note that the same reference numerals as those in the first embodiment (Fig. 1) denote the same parts. --

Please substitute the paragraph beginning at page 24, line 7, and ending on page 25, line 3, with the following.

-- The manufacturing process of a semiconductor device using the above-mentioned electron beam exposure apparatuses will be described next. Fig. 8 shows the flow of the whole manufacturing process of the semiconductor device. In step 1 (circuit design), a semiconductor device circuit is designed. In step 2 (exposure control data creation), exposure control data for exposure control (e.g., the on/off control of electron beams) is created on the basis of the designed circuit pattern. In step 3 (wafer manufacture), a wafer is manufactured by using a material such as silicon. In step 4 (wafer process), called a preprocess, an actual circuit is formed on the wafer by lithography using the above-mentioned electron beam exposure apparatuses in the exposure step. Step 5 (assembly), called a post-process, is the step of forming a

semiconductor chip by using the wafer formed in step 4, and includes an assembly process (dicing and bonding) and a packaging process (chip encapsulation). In step 6 (inspection), the semiconductor device manufactured in step 5 undergoes inspections such as an operation confirmation test and a durability test. After these steps, the semiconductor device is completed and shipped (step 7). --